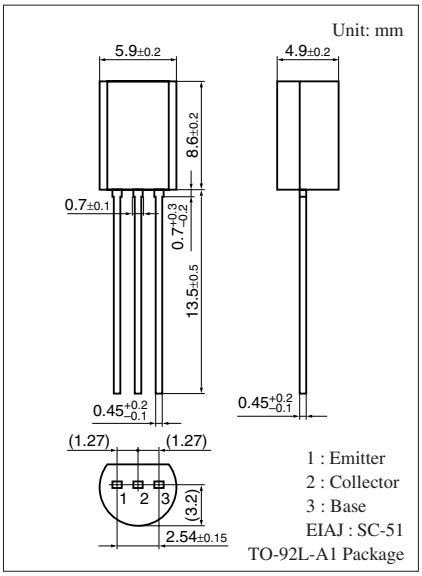
2SA0777 (2SA777)

Silicon PNP epitaxial planar type

For low-frequency driver amplification
Complementary to 2SC1509



■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- Optimum for the driver stage of a low-frequency and 25 W to 30 W output amplifier.

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	−80	V
Collector-emitter voltage (Base open)	V_{CEO}	−80	V
Emitter-base voltage (Collector open)	V_{EBO}	−5	V
Collector current	I_C	− 0.5	A
Peak collector current	I_{CP}	−1	A
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

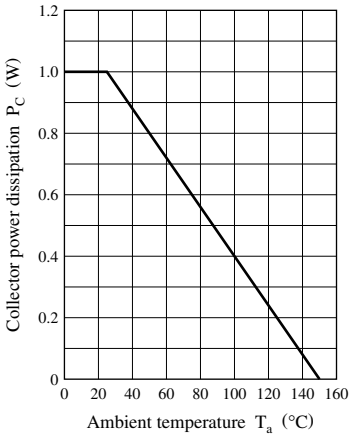
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10$ µA, $I_E = 0$	−80			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -100$ µA, $I_B = 0$	−80			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -1$ µA, $I_C = 0$	−5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20$ V, $I_E = 0$			− 0.1	µA
Forward current transfer ratio *1	h_{FE1} *2	$V_{CE} = -10$ V, $I_C = -150$ mA	90		220	—
	h_{FE2}	$V_{CE} = -5$ V, $I_C = -500$ mA	50	100		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500$ mA, $I_B = -50$ mA		− 0.2	− 0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500$ mA, $I_B = -50$ mA		− 0.85	−1.2	V
Transition frequency	f_T	$V_{CB} = -10$ V, $I_E = 50$ mA, f = 200 MHz		120		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz		11	20	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. ∗1: Palse measurement
∗2: Rank classification

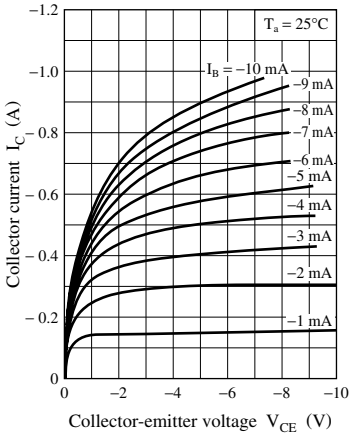
Rank	Q	R
h_{FE1}	90 to 155	130 to 220

Note) The part number in the parenthesis shows conventional part number.

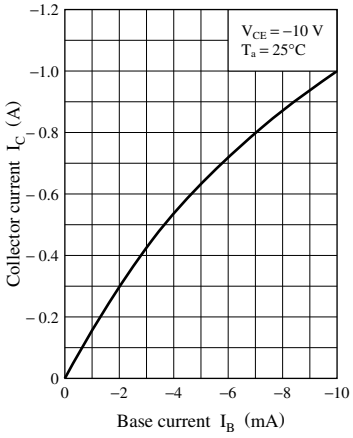
P_C — T_a



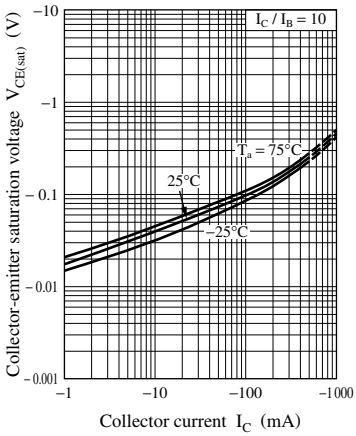
I_C — V_{CE}



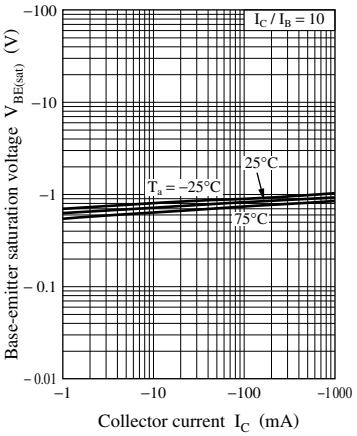
I_C — I_B



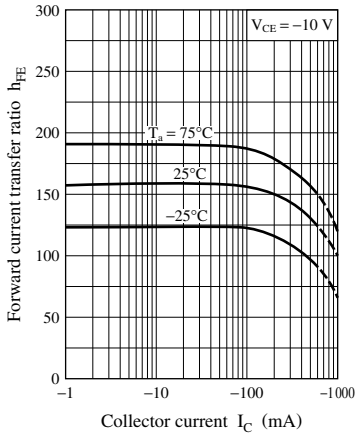
$V_{CE(sat)}$ — I_C



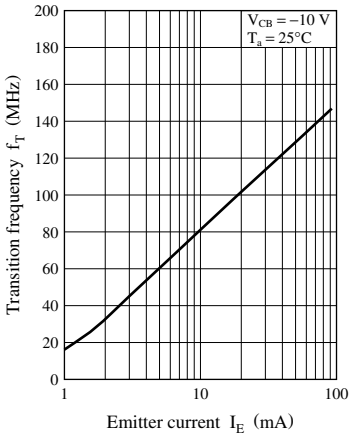
$V_{BE(sat)}$ — I_C



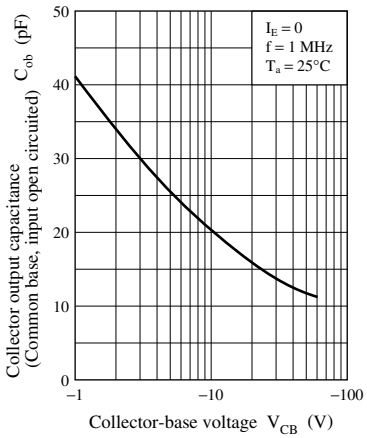
h_{FE} — I_C



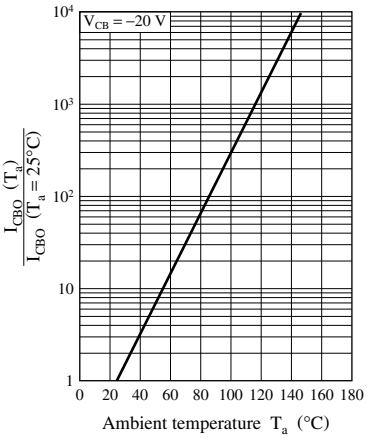
f_T — I_E



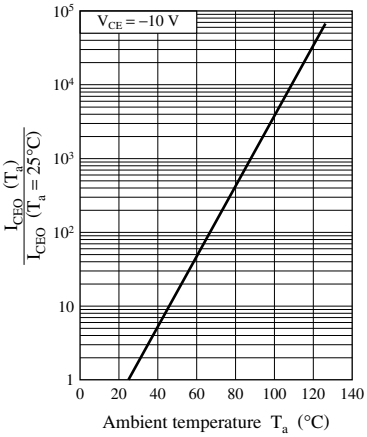
C_{ob} — V_{CB}



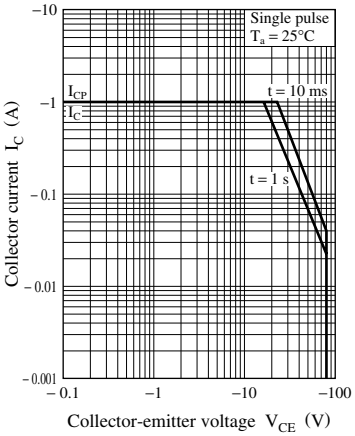
I_{CBO} — T_a



I_{CEO} — T_a



Safe operation area



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